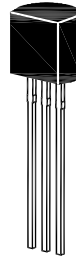


**FUKUCOM COMPANY LTD.****福 靈 有 限 公 司**FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
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BC212**PNP Silicon Epitaxial Planar Transistor**

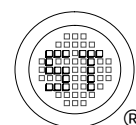
for general purpose amplifier

1. Emitter 2. Collector 3. Base
TO-92 Plastic Package**Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)**

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	300	mA
Total Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ }\mu\text{A}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$	h_{FE} h_{FE}	40 60	- 300	- -
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	15	nA
Emitter Base Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	15	nA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	60	-	V
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	50	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	0.6	V
Base Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{BE(sat)}$	-	1.1	V
Base Emitter On Voltage at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$	$-V_{BE(on)}$	0.6	0.72	V
Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	200	-	MHz
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{CBO}	-	10	pF



Dated : 27/12/2007